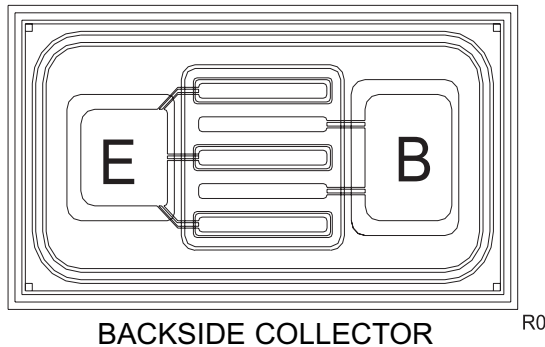


**PROCESS DETAILS**

|                          |                  |
|--------------------------|------------------|
| Process                  | EPITAXIAL PLANAR |
| Die Size                 | 12 x 20 MILS     |
| Die Thickness            | 7.1 MILS         |
| Base Bonding Pad Area    | 3.6 X 3.6 MILS   |
| Emitter Bonding Pad Area | 3.6 X 3.6 MILS   |
| Top Side Metalization    | Al - 30,000Å     |
| Back Side Metalization   | Au - 18,000Å     |

**GEOMETRY**



**GROSS DIER PER 4 INCH WAFER**

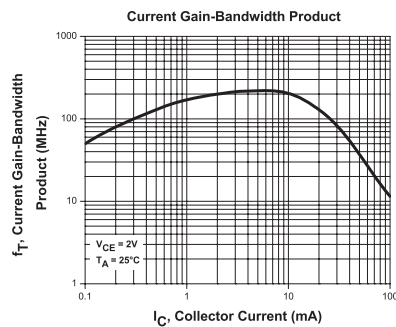
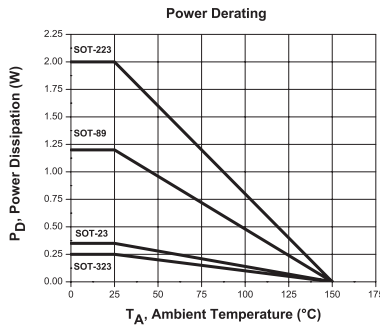
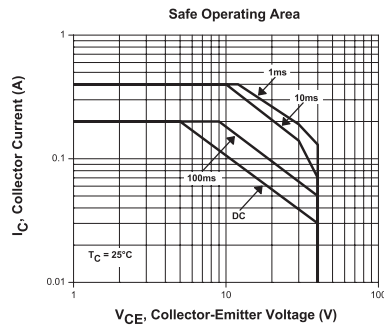
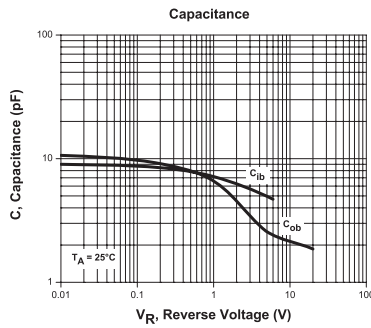
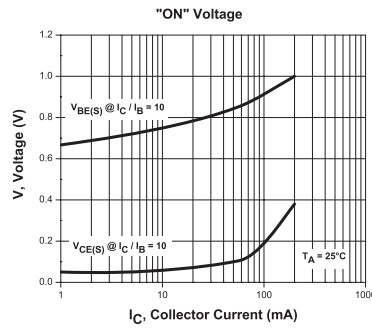
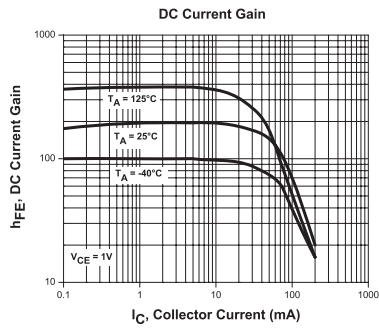
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**PRINCIPAL DEVICE TYPES**

2N3906  
CMKT3906  
CMLT3906E  
CMPT3906  
CMST3906  
CXT3906  
CZT3906

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R2 (8- October 2008)



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